

GaAs IC SPDT Switch Non-Reflective DC–6 GHz



AS006M2-01, AS006M2-10

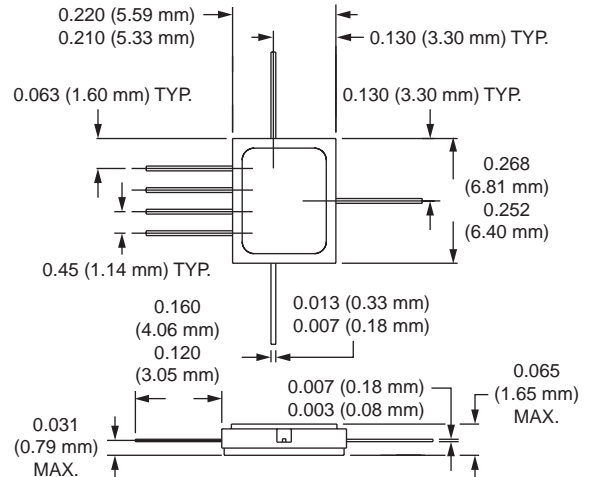
Features

- Low DC Power Consumption
- High Isolation, Non-Reflective
- 7 Lead Hermetic Package
- Capable of Meeting MIL-STD Requirements⁵

Description

The AS006M2-01 is a GaAs IC FET SPDT non-reflective switch. This device is ideal for microstrip applications and has optimum performance at higher frequencies (4–6 GHz), since all leads are RF isolated. This product is useful as a modulator and switch in high reliability and commercial applications. The AS006M2-10 is the gullwing version of this device for surface mount applications.

-01



Electrical Specifications at 25°C

Parameter ¹	Frequency ⁴	Min.	Typ.	Max.	Unit
Insertion Loss ²	DC–1.0 GHz		0.8	1.0	dB
	DC–2.0 GHz		1.0	1.2	dB
	DC–4.0 GHz		1.4	1.6	dB
	DC–6.0 GHz		1.7	1.9	dB
Isolation	DC–1.0 GHz	55	63		dB
	DC–2.0 GHz	50	57		dB
	DC–4.0 GHz	34	40		dB
	DC–6.0 GHz	20	26		dB
VSWR (I/O)	DC–1.0 GHz		1.2:1	1.3:1	
	DC–2.0 GHz		1.3:1	1.5:1	
	DC–4.0 GHz		1.6:1	1.8:1	
	DC–6.0 GHz		1.8:1	2.0:1	

Operating Characteristics at 25°C

Parameter	Condition	Frequency	Min.	Typ.	Max.	Unit
Switching Characteristics	Rise, Fall (10/90% or 90/10% RF) On, Off (50% CTL to 90/10% RF) Video Feedthru ³			3	6	ns
				6	10	ns
				20	30	mV
Input Power for 1 dB Compression	0/-5 V (0/-8 V)	0.5–6 GHz	21	24 (30)		dBm
		0.001 GHz	12	16 (20)		dBm
Intermodulation Intercept Point (IP3)	For Two-tone Input Power 13 dBm	0.5–6 GHz	42	46		dBm
		0.001 GHz	32	35		dBm
Control Voltages	$V_{Low} = 0 \text{ to } -0.2 \text{ V @ } 20 \mu\text{A Max.}$ $V_{High} = -5 \text{ V @ } 50 \mu\text{A to } -9 \text{ V @ } 200 \mu\text{A Max.}$					

1. All measurements made in a 50 Ω system, unless otherwise specified.

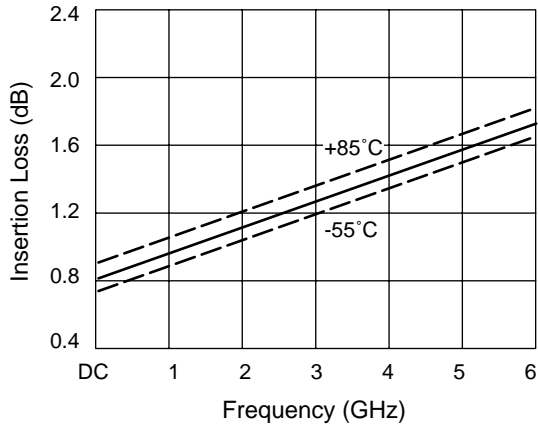
2. Insertion loss changes by 0.003 dB/°C.

3. Video feedthru measured with 1 ns risetime pulse and 500 MHz bandwidth.

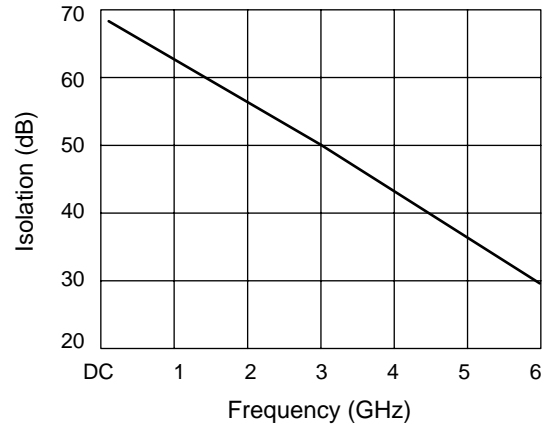
4. DC = 300 kHz.

5. See Quality/Reliability section.

Typical Performance Data



Insertion Loss vs. Frequency



Isolation vs. Frequency

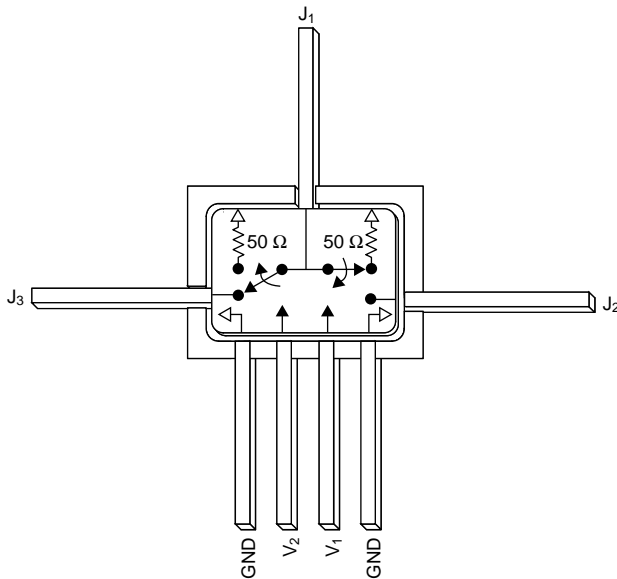
Truth Table

V ₁	V ₂	J ₁ –J ₂	J ₁ –J ₃
-5	0	Insertion Loss	Isolation
0	-5	Isolation	Insertion Loss

Absolute Maximum Ratings

Characteristic	Value
RF Input Power (RF In)	2 W > 500 MHz 0/-8 V 0.5 W @ 50 MHz 0/-8 V
Control Voltage (V _C)	+0.2 V, -10.0 V
Operating Temperature (T _{OP})	-55°C to +125°C
Storage Temperature (T _{ST})	-65°C to +150°C
Thermal Resistance (Θ _{JC})	25°C/W

Pin Out



-10

